

Amendment to the Claims

Claims 1-17 (Cancelled)

18. **(Previously Presented)** A method of mounting a semiconductor laser device comprising:

heating a bonding member to be fused on a submount by heating a table upon which said submount is mounted;

holding a semiconductor laser component with a collet;

pressure bonding said semiconductor laser component in a loading position on said submount with said collet so as to mount said semiconductor laser component on said submount; and

terminating the heating operation while the collet pressure bonds the semiconductor laser component to the submount,

wherein the pressure bonding operation is carried out so as to substantially prevent transfer of heat from said semiconductor laser component to said collet,

wherein said collet has a contacting side having an area larger than that of a contacting portion of said semiconductor laser component.

19. **(Previously Presented)** The method of mounting a semiconductor laser device according to claim 18, further comprising heating the collet to substantially the same temperature as that of the heating table while the heating table is heated so as to prevent transfer of heat from said semiconductor laser component to said collet.

20.(**Previously Presented**) The method of mounting a semiconductor laser device according to claim 18, wherein said collet is maintained at a temperature higher than the temperature of said heating table until said bonding member solidifies completely.

21.(**Previously Presented**) The method of mounting a semiconductor laser device according to claim 18, wherein said semiconductor laser component is heated to substantially the same temperature as the temperature of said collet before said semiconductor laser component is held by said collet.

22.(**Previously Presented**) The method of mounting a semiconductor laser device according to claim 18, wherein said semiconductor laser component is released from said collet when a part of said bonding member solidifies but prior to complete solidification of the bonding member.

23.(**Previously Presented**) The method of mounting a semiconductor laser device according to claim 22, wherein said bonding member comprises two or more kinds of materials having different fusing points.

24.(**Previously Presented**) A method of mounting a semiconductor laser device comprising:

heating a bonding member to be fused on a submount by heating a table upon

which said submount is mounted;

holding a semiconductor laser component with a collet;

pressure bonding said semiconductor laser component in a loading position on said submount with said collet so as to mount said semiconductor laser component on said submount; and

terminating the heating operation while the collet pressure bonds the semiconductor laser component to the submount,

wherein the pressure bonding operation is carried out so as to substantially prevent transfer of heat from said semiconductor laser component to said collet,

wherein said semiconductor laser component is released from said collet when a part of said bonding member solidifies but prior to complete solidification of the bonding member,

wherein a part of said bonding member is solidified by forced air cooling during pressure bonding of said semiconductor laser component by said collet.

25.(Previously Presented) The method of mounting a semiconductor laser device according to claim 18, wherein said bonding member has a fusing point lower than that of an eutectic solder.

26.(Previously Presented) The method of mounting a semiconductor laser device according to claim 18, wherein after said bonding member has solidified, the bonding member is heated again to a temperature higher than the fusing point.

27.(Previously Presented) The method of mounting a semiconductor laser device according to claim 18, wherein said collet has a contacting side having an area larger than that of a contacting portion of said semiconductor laser component.

28.(Previously Presented) The method of mounting a semiconductor laser device according to claim 18, wherein said collet has a contacting side face, and a part of said side face contacts the semiconductor laser component and is made of a material with low heat conductivity.

29.(Previously Presented) The method of mounting a semiconductor laser device according to claim 18, wherein said semiconductor component is bonded near a macro-axis side thereof on said submount by said bonding member and the remaining parts contact said submount through a heat transmission member.

30.(Previously Presented) A method of mounting a semiconductor laser device comprising:

heating a bonding member to be fused on a submount by heating a table upon which said submount is mounted;

holding a semiconductor laser component with a collet; and

pressure bonding said semiconductor laser component in a loading position on said submount with said collet so as to mount said semiconductor laser component on

said submount; and

releasing said semiconductor laser component from said collet upon solidification of only a part of said bonding member.

31.(Previously Presented) The method of mounting a semiconductor laser device according to claim 30, wherein said bonding member comprises two or more kinds of materials having different fusing points.

32.(Previously Presented) The method of mounting a semiconductor laser device according to claim 30, wherein a part of said bonding member is solidified by means of forced air cooling during pressure bonding of said semiconductor laser component by said collet.

33.(Previously Presented) A method of mounting a semiconductor laser device comprising:

heating a bonding member to be fused on a submount by heating a table on which said submount is mounted;

holding a semiconductor laser component with a collet; and

pressure bonding said semiconductor laser component in a loading position on said submount with said collet so as to mount said semiconductor laser component on said submount,

wherein said bonding member has a fusing point that is lower than that of an

eutectic solder.

34.(Previously Presented) The method of mounting a semiconductor laser device according to claim 19, wherein the heating of the table and the collet are simultaneously terminated.

35.(New) A method of mounting a semiconductor laser device comprising:

heating a bonding member to be fused on a submount by heating a table upon which said submount is mounted;

holding a semiconductor laser component with a collet;

pressure bonding said semiconductor laser component in a loading position on said submount with said collet so as mount said semiconductor laser component on said submount; and

terminating the heating while the collet pressure bonds the semiconductor laser component to the submount,

wherein the pressure bonding operation is carried out so as to substantially prevent transfer of heat from said semiconductor laser component to said collet,

wherein said collet has a contacting side having an outer edge portion all of which is positioned out of an outer edge portion of a contacting face of said semiconductor laser component.

36.(New) The method of mounting a semiconductor laser device according to claim

35, further comprising the collect to substantially the same temperature as that of the heating table while the heating table is heated so as to prevent transfer of heat from said semiconductor laser component to said collet.

37.(New) The method of mounting a semiconductor laser device according to claim 35, wherein said collet is maintained at a temperature higher than the temperature of said heating table until said bonding member solidifies completely.

38.(New) The method of mounting a semiconductor laser device according to claim 35, wherein said semiconductor laser component is heated to substantially the same temperature as the temperature of said collet before said semiconductor laser component is hold by said collet.

39.(New) The method of mounting a semiconductor laser device according to claim 35, wherein said semiconductor laser component is released from said collet when a part of said bonding member solidifies but prior to complete solidification of the bonding member.

40.(New) The method of mounting a semiconductor laser device according to claim 35, wherein said bonding member comprises two or more kinds of the materials having different fusing points.

41. (New) A method of mounting a semiconductor laser device comprising:

heating a bonding member to be fused on a submount by heating a table upon which said submount is mounted;

holding a semiconductor laser component with a collet;

heating the collet;

pressure bonding said semiconductor laser component in a loading position on said submount with said collet so as to mount said semiconductor laser component on said submount; and

terminating the heating while the collet pressure bonds the semiconductor laser component to the submount,

wherein the pressure bonding operation is carried out so as to substantially prevent transfer of heat from said semiconductor laser component to said collet,

wherein said collet and said table are heated up to the same temperature when said collet and said table are heated and said collet and said table are cooled under a same temperature profile when the semiconductor laser device is cooled.